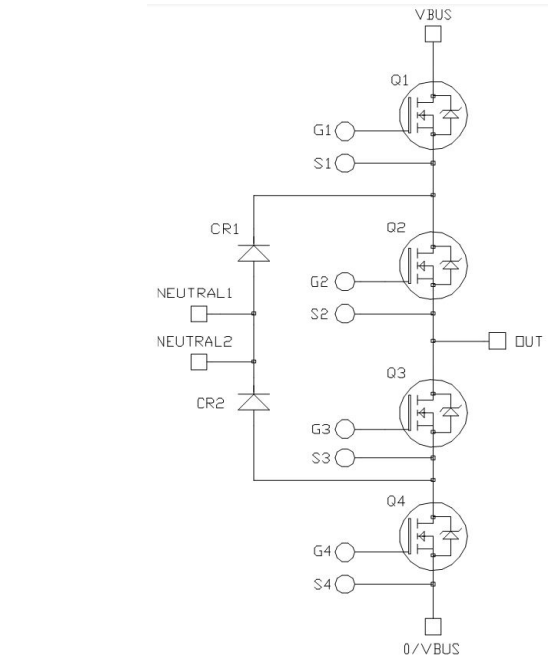
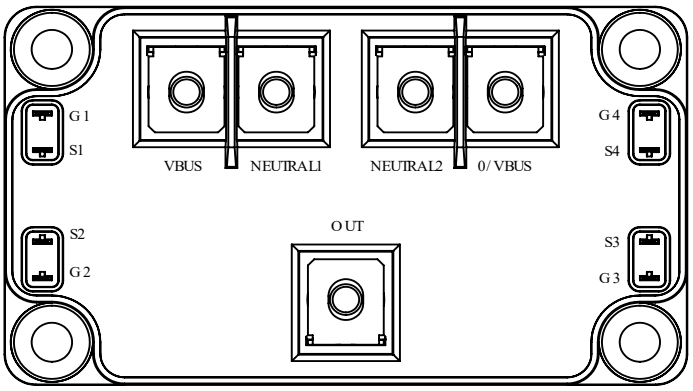
MSCSM120TLM11CAG

Three Level Inverter SiC MOSFET Power Module

Product Overview

The MSCSM120TLM11CAG device is a three level inverter 1200V/251A silicon carbide (SiC) MOSFET power module.





Note: All ratings at T_J = 25 °C, unless otherwise specified.

⚠ CAUTION These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are key features of the MSCSM120TLM11CAG device:

- SiC Power MOSFET
  - Low $R_{DS(on)}$
  - High temperature performance
- SiC Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature independent switching behavior
  - Positive temperature coefficient on VF
- Low stray inductance
- Kelvin source for easy drive
- M5 power connectors
- High level of integration
- Aluminum nitride (AlN) substrate for improved thermal performance

Benefits

The following are the benefits of MSCSM120TLM11CAG device:

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Low profile
- RoHS Compliant

Application

The MSCSM120TLM11CAG device is designed for the following applications:

- Solar converter
- Uninterruptible power supplies

Electrical Specifications

This section provides the electrical specifications of the MSCSM120TLM11CAG device.

SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM120TLM11CAG device.

Table 1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
V_{DSS}	Drain-Source voltage		1200	V
I_D	Continuous drain current	T_C = 25 °C	251	A
		T_C = 80 °C	200	
I_{DM}	Pulsed drain current		500	
V_{GS}	Gate-Source voltage		–10/25	V
$R_{DS(on)}$	Drain-Source ON resistance		10.4	mΩ
P_D	Power dissipation	T_C = 25 °C	1042	W

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM120TLM11CAG device.

Table 2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0V; V_{DS} = 1200V		—	30	300	µA
$R_{DS(on)}$	Drain–Source on resistance	V_{GS} = 20V	T_J = 25 °C	—	8.3	10.4	mΩ
		I_D = 120A	T_J = 175 °C	—	13.3	—	
$V_{GS(th)}$	Gate threshold voltage	V_{GS} = V_{DS}; I_D = 3 mA		1.8	2.8	—	V
I_{GSS}	Gate–Source leakage current	V_{GS} = 20V; V_{DS} = 0V		—	—	300	nA

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM120TLM11CAG device.

Table 3. Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{GS} = 0V		—	9	—	nF
C_{oss}	Output capacitance	V_{DS} = 1000V		—	0.81	—	
C_{rss}	Reverse transfer capacitance	f = 1 MHz		—	0.07	—	
Q_g	Total gate charge	V_{GS} = –5V/20V		—	696	—	nC
Q_{gs}	Gate-source charge	V_{Bus} = 800V		—	123	—	
Q_{gd}	Gate-drain charge	I_D = 120A		—	150	—	
$T_{d(on)}$	Turn-on delay time	V_{GS} = –5V/20V	T_J = 150 °C	—	56	—	ns
T_r	Rise time	V_{Bus} = 600V		—	55	—	
$T_{d(off)}$	Turn-off delay time	I_D = 150A		—	166	—	
T_f	Fall time	$R_{G(on)}$ = 2.7Ω $R_{G(off)}$ = 1.6Ω		—	67	—	
E_{on}	Turn-on energy	V_{GS} = –5V/20V	T_J = 150 °C	—	3	—	mJ
E_{off}	Turn-off energy	V_{Bus} = 600V I_D = 150A $R_{G(on)}$ = 2.7Ω $R_{G(off)}$ = 1.6Ω	T_J = 150 °C	—	2.7	—	
R_{Gint}	Internal gate resistance			—	2	—	Ω
R_{thJC}	Junction-to-case thermal resistance			—	—	0.144	°C/W

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM120TLM11CAG device.

Table 4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode forward voltage	V_{GS} = 0V; I_{SD} = 120A	—	4	—	V
		V_{GS} = –5V; I_{SD} = 120A	—	4.2	—	
t_{rr}	Reverse recovery time	I_{SD} = 120A; V_{GS} = –5V	—	90	—	ns
Q_{rr}	Reverse recovery charge	V_R = 800V; di_F/dt = 3000 A/µs	—	1650	—	nC
I_{rr}	Reverse recovery current		—	41	—	A

CR1 and CR2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the CR1 and CR2 SiC diode ratings and characteristics per SiC diode of MSCSM120TLM11CAG device.

Table 5. SiC Schottky Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
V_{RRM}	Peak repetitive reverse voltage			—	—	1200	V
I_{RRM}	Reverse leakage current	V_R = 1200V	T_J = 25 °C	—	45	600	µA
			T_J = 175 °C	—	750	—	
I_F	DC forward current	—	T_C = 100 °C	—	150	—	A
V_F	Diode forward voltage	I_F = 150A	T_J = 25 °C	—	1.5	1.8	V
			T_J = 175 °C	—	2.1	—	
Q_C	Total capacitive charge	V_R = 600V		—	672	—	nC
C	Total capacitance	f = 1 MHz, V_R = 400V		—	738	—	pF
		f = 1 MHz, V_R = 800V		—	546	—	
R_{thJC}	Junction-to-case thermal resistance			—	—	0.212	°C/W

Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM120TLM11CAG device.

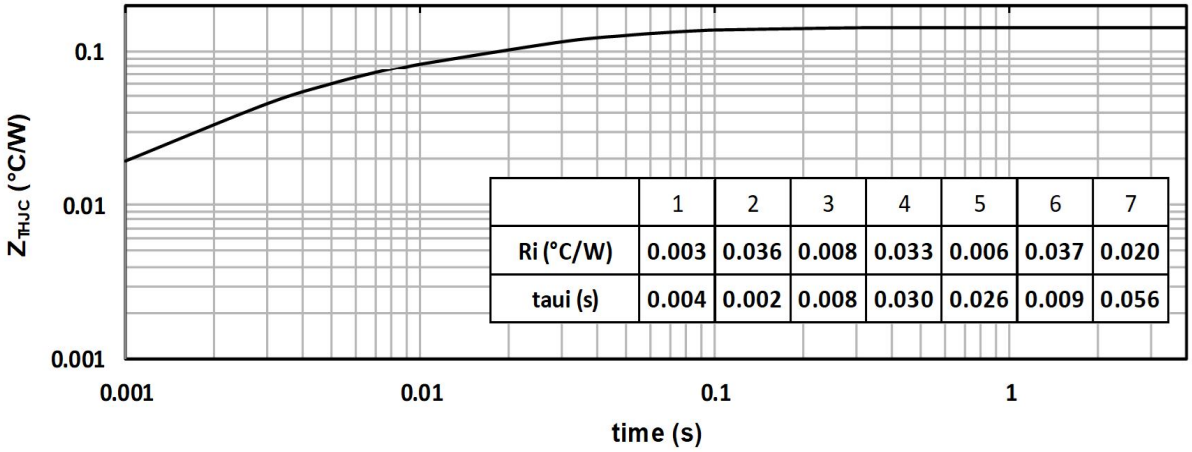
Table 6. Thermal and Package Characteristics

Symbol	Characteristics			Min.	Max.	Unit
V_{ISOL}	RMS isolation voltage, any terminal to case t =1 min, 50 Hz/60 Hz			4000	—	V
T_J	Operating junction temperature range			–40	175	°C
T_{JOP}	Recommended junction temperature under switching conditions			–40	T_{Jmax}–25	
T_{STG}	Storage temperature range			–40	125	
T_C	Operating case temperature			–40	125	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package weight			—	300	g

Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM120TLM11CAG device.

Figure 1. Maximum Thermal Impedance



	1	2	3	4	5	6	7
Ri (°C/W)	0.003	0.036	0.008	0.033	0.006	0.037	0.020
taui (s)	0.004	0.002	0.008	0.030	0.026	0.009	0.056

Figure 2. Output Characteristics, T_J = 25 °C

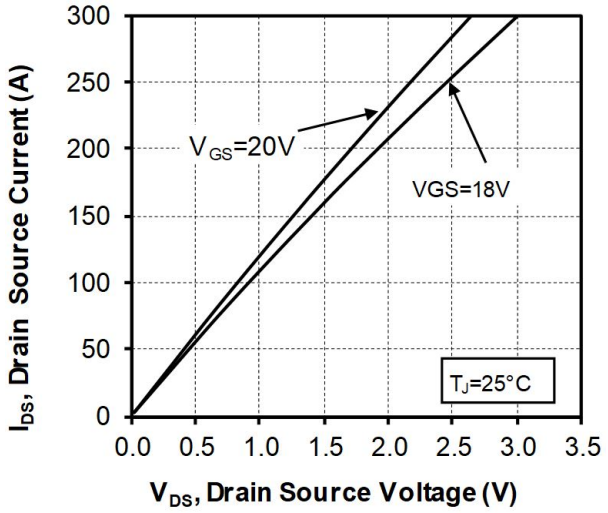


Figure 3. Output Characteristics, T_J = 175 °C

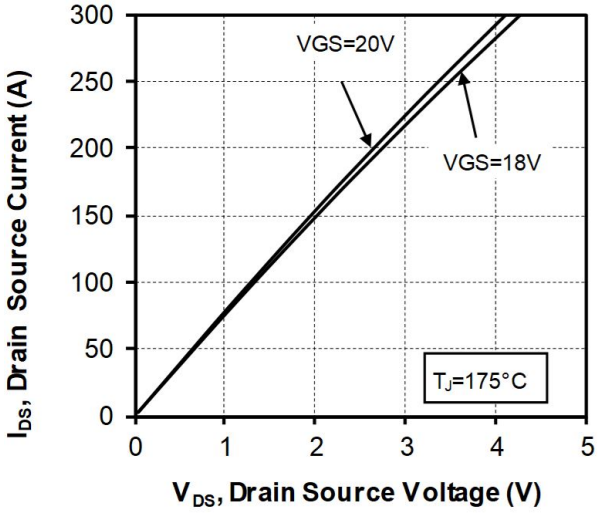


Figure 4. Normalized $R_{DS(on)}$ vs. Temperature

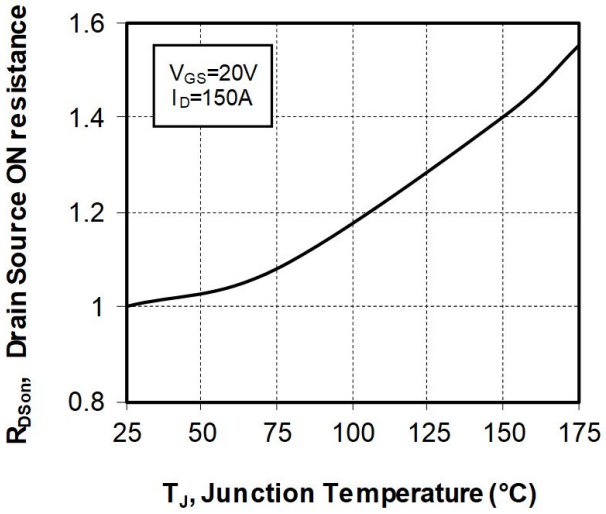


Figure 5. Transfer Characteristics

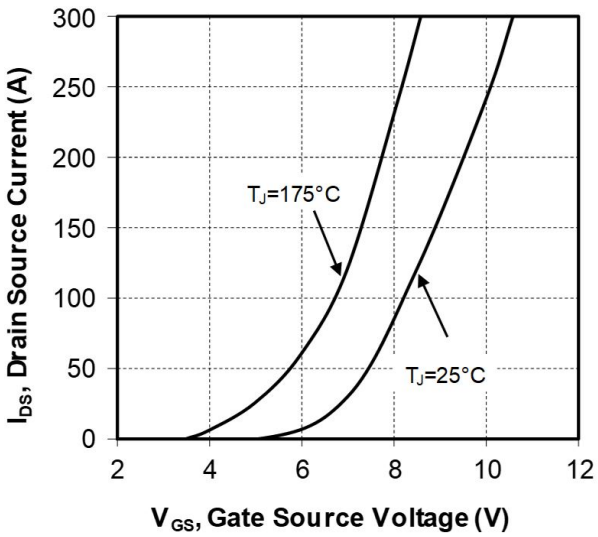


Figure 6. Switching Energy vs. Rg

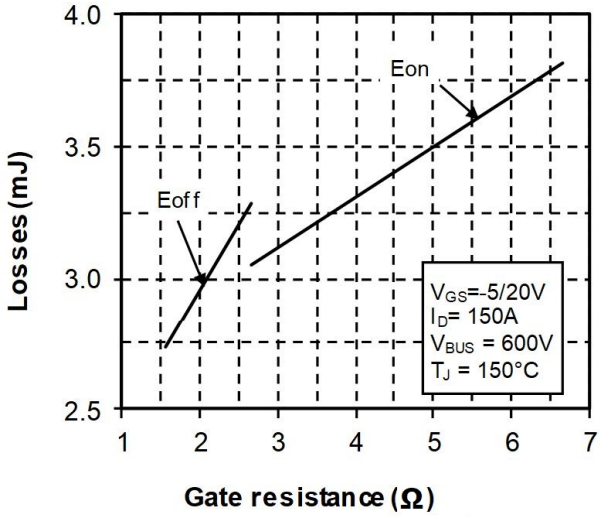


Figure 7. Switching Energy vs. Current

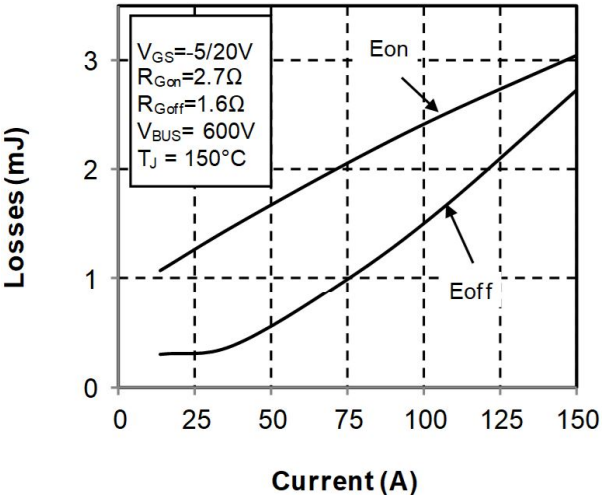


Figure 8. Capacitance vs. Drain Source Voltage

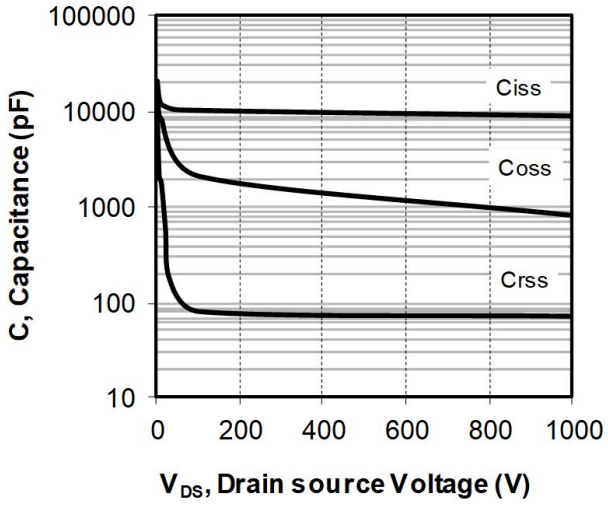


Figure 9. Gate Charge vs. Gate Source Voltage

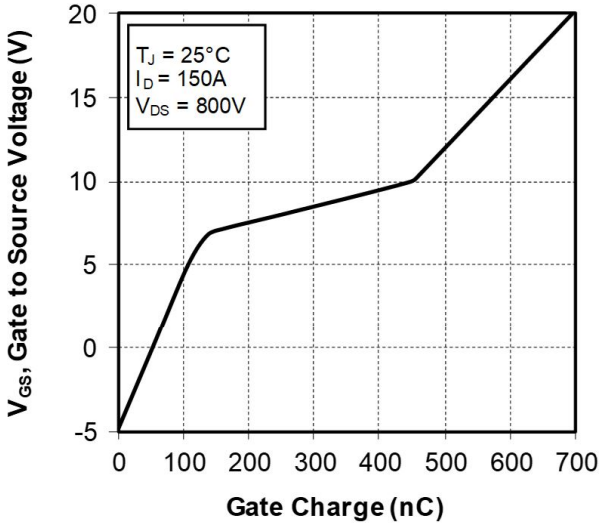


Figure 10. Body Diode Characteristics, T_J = 25 °C

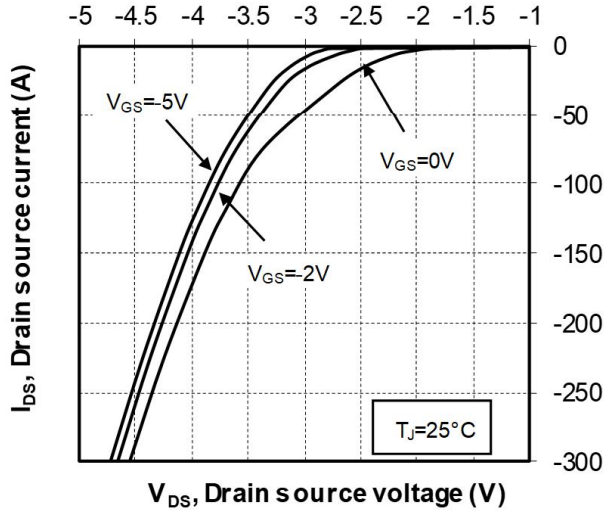


Figure 11. 3rd Quadrant Characteristics, T_J = 25 °C

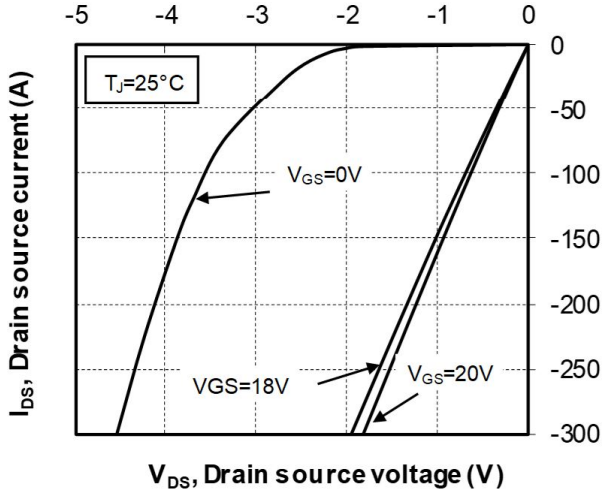


Figure 12. Body Diode Characteristics, T_J = 175 °C

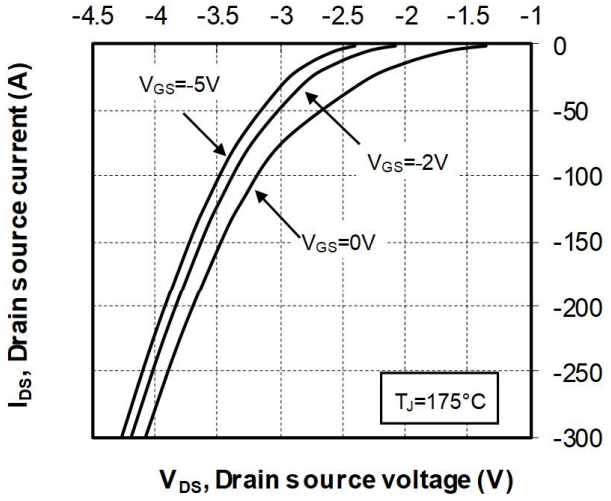


Figure 13. 3rd Quadrant Characteristics, T_J = 175 °C

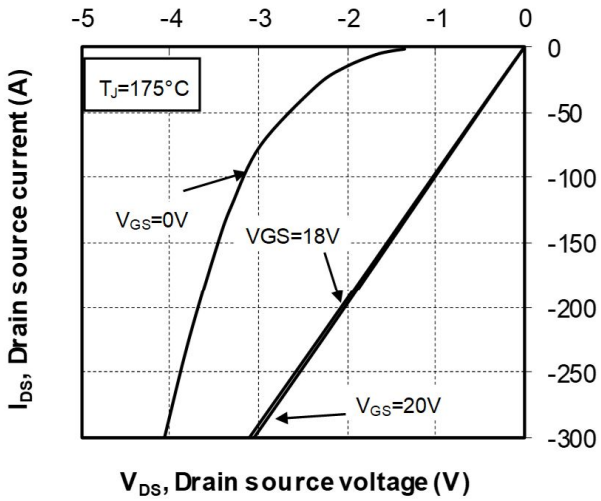
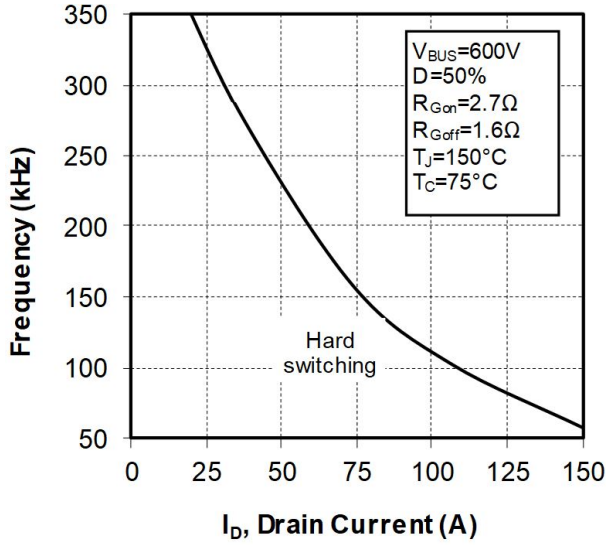


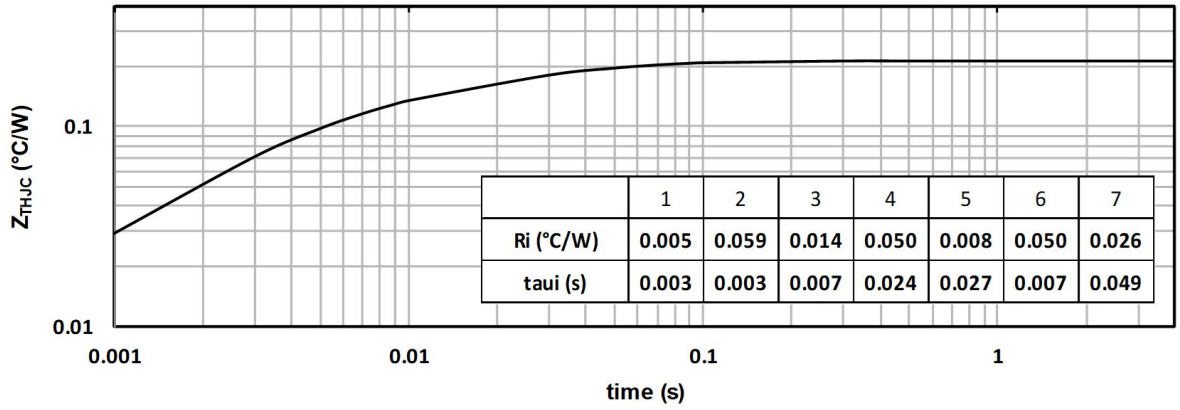
Figure 14. Operating Frequency vs Drain Current



Typical SiC Diode Performance Curves

This section shows the typical SiC diode performance curves of the MSCSM120TLM11CAG device.

Figure 15. Maximum Thermal Impedance



	1	2	3	4	5	6	7
Ri (°C/W)	0.005	0.059	0.014	0.050	0.008	0.050	0.026
taui (s)	0.003	0.003	0.007	0.024	0.027	0.007	0.049

Figure 16. Forward Characteristics

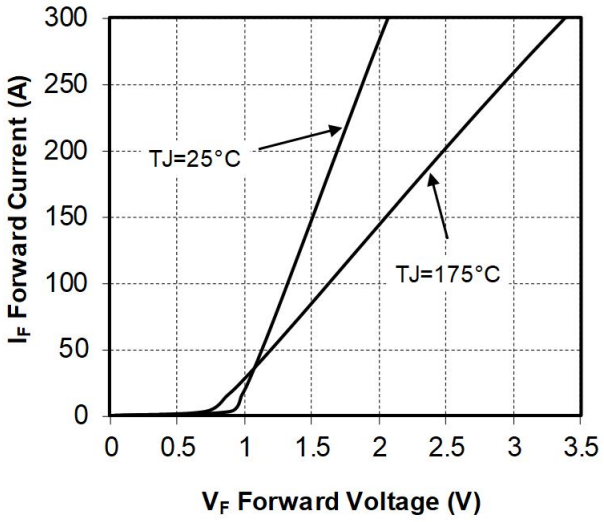
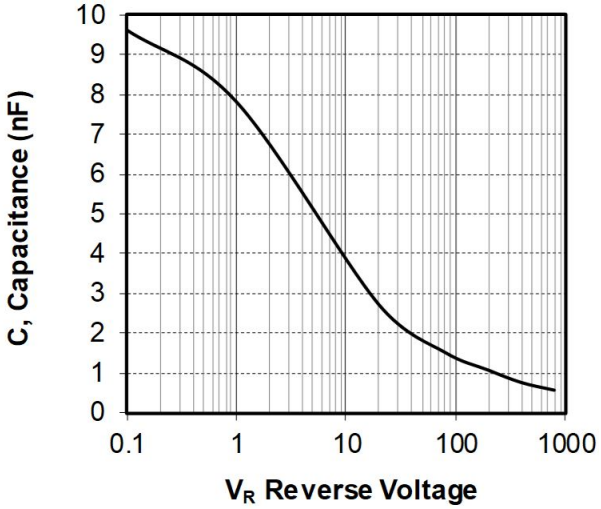


Figure 17. Capacitance vs. Reverse Voltage



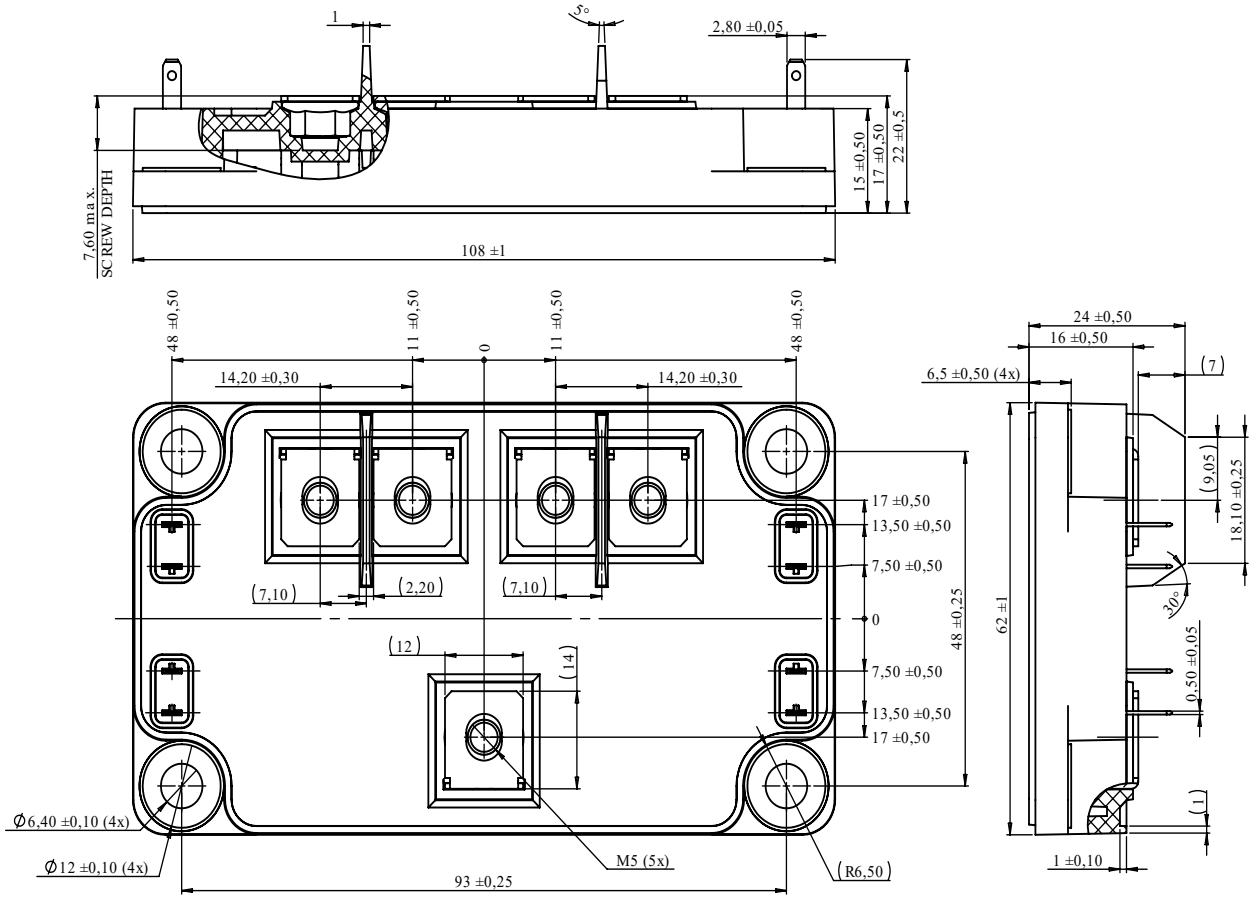
Package Specifications

The following section shows the package specification of the MSCSM120TLM11CAG device.

Package Outline

The following figure shows the package outline drawing of the MSCSM120TLM11CAG device. The dimensions in the following figure are in millimeters.

Figure 18. Package Outline Drawing



Revision History

Revision	Date	Description
A	12/2021	This is the first publication of this document.

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